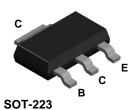


BCP55



NPN General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switching circuits requiring collector currents to 1.0 A. Sourced from Process 38. See BCP54 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	1.5	А
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

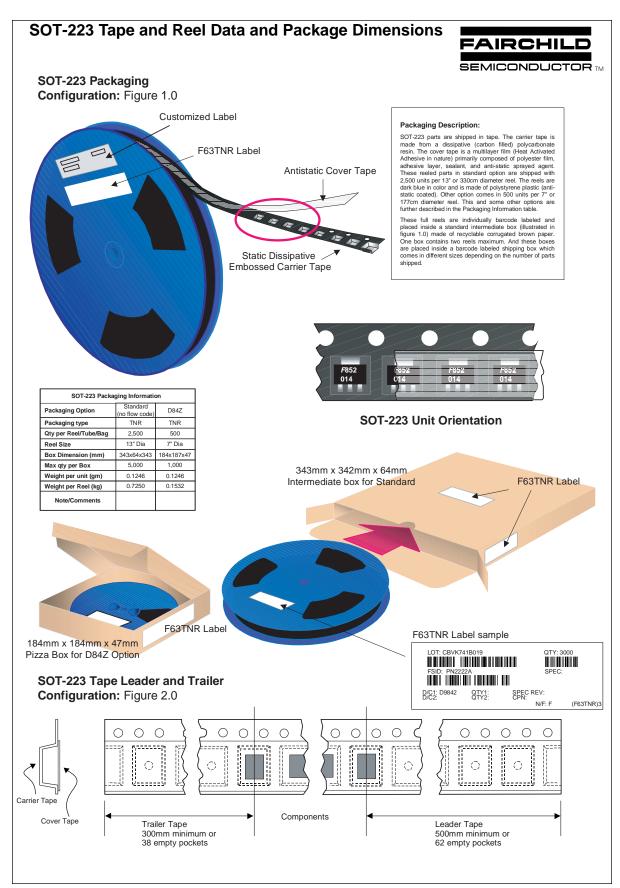
Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units	
		BCP55		
P _D	Total Device Dissipation	1.5	W	
	Derate above 25°C	12	mW/°C	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	83.3	°C/W	

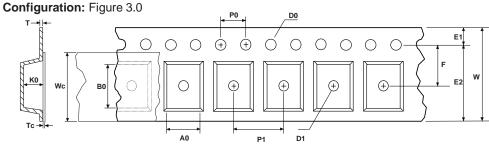
NPN General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	60		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	Ic = 100 μA, I _E = 0	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5.0		V
I _{CBO}	Collector-Cutoff Current	V _{CB} = 30 V, I _E = 0 V _{CB} = 30 V, I _E = 0, T _A = 125°C		100 10	nA μA
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$		10	μA
I _{EBO}		$V_{CB} = 30 \text{ V}, I_{E} = 0, T_{A} = 125^{\circ}\text{C}$		10	
h _{FE}	DC Current Gain	$I_C = 5.0 \text{ mA}, V_{CE} = 2.0 \text{ V}$	25		
****	Do ourion ouri	$I_C = 5.0 \text{ mA}, V_{CE} = 2.0 \text{ V}$ $I_C = 150 \text{ mA}, V_{CE} = 2.0 \text{ V}$ $I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V}$	40 25	250	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 500 mA, I _B = 50 mA		0.5	V
V _{RE(on)}	Base-Emitter On Voltage	Ic = 500 mA. VcE = 2.0 V	1.0	V	





SOT-223 Embossed Carrier Tape



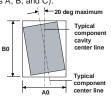
User Direction of Feed	
	$\overline{}$

	Dimensions are in millimeter													
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOT-223 (12mm)	6.83 +/-0.10	7.42 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.50 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	1.88 +/-0.10	0.292 +/- 0.0130	9.5 +/-0.025	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



Sketch B (Top View)
Component Rotation

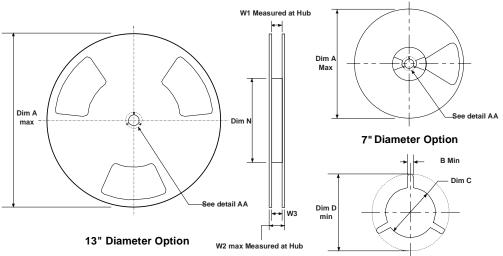


Sketch C (Top View)

Component lateral movement

DETAIL AA

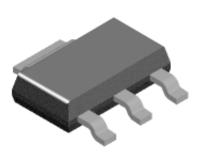
SOT-223 Reel Configuration: Figure 4.0

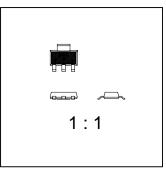


	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	5.906 150	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

SOT-223 Tape and Reel Data and Package Dimensions, continued

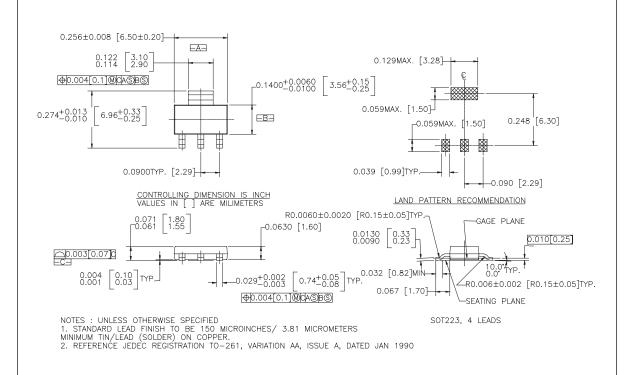
SOT-223 (FS PKG Code 47)





Scale 1:1 on letter size paper

Part Weight per unit (gram): 0.1246



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